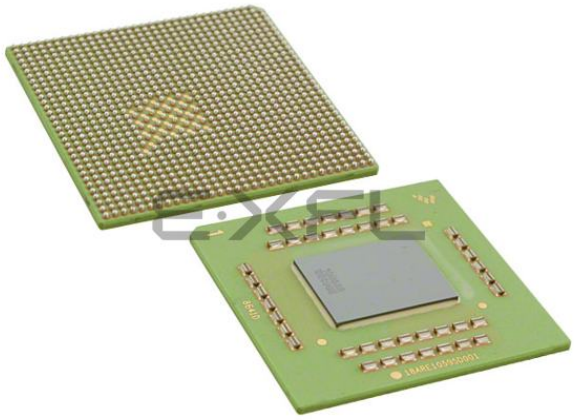


Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641tvu1000gc

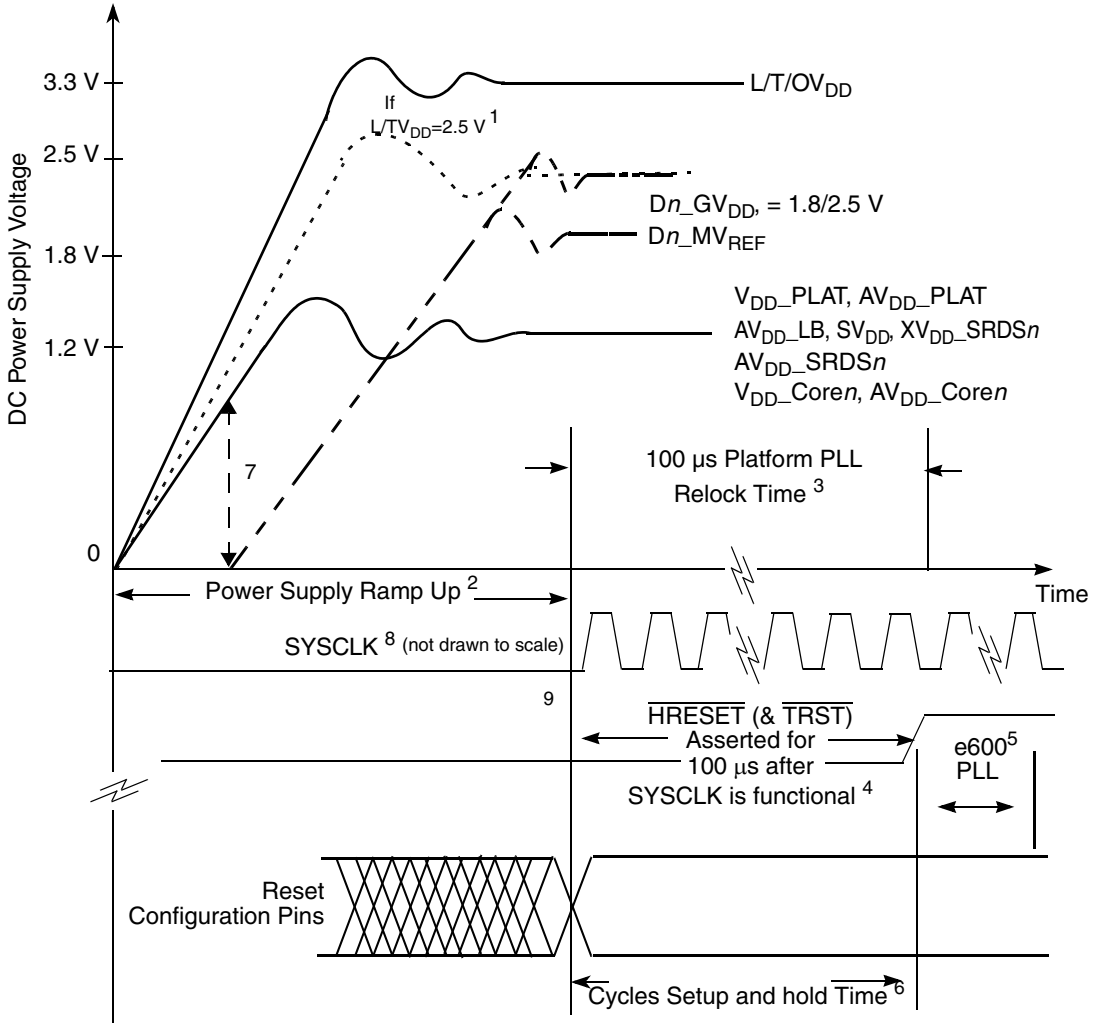
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
Junction temperature range	T_J	0 to 105	°C	—

Notes:

1. Core 1 characteristics apply only to MPC8641D
2. If two separate power supplies are used for V_{DD}_Core0 and V_{DD}_Core1, they must be at the same nominal voltage and the individual power supplies must be tracked and kept within 100 mV of each other during normal run time.
3. **Caution:** D*n*_MV_{IN} must meet the overshoot/undershoot requirements for D*n*_GV_{DD} as shown in Figure 2.
4. **Caution:** L/TV_{IN} must meet the overshoot/undershoot requirements for L/TV_{DD} as shown in Figure 2 during regular run time.
5. **Caution:** OV_{IN} must meet the overshoot/undershoot requirements for OV_{DD} as shown in Figure 2 during regular run time.
6. Timing limitations for M,L,T,O)V_{IN} and D*n*_MV_{REF} during regular run time is provided in Figure 2
7. Applies to devices marked with a core frequency of 1333 MHz and below. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency of 1333 MHz and below.
8. Applies to devices marked with a core frequency above 1333 MHz. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for a core frequency above 1333 MHz.
9. The 2.5 V ± 125 mV range is for DDR and 1.8 V ± 90 mV range is for DDR2.
10. See Section 8.2, "FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications," for details on the recommended operating conditions per protocol.
11. The PCI Express interface of the device is expected to receive signals from 0.175 to 1.2 V. For more information refer to Section 14.4.3, "Differential Receiver (RX) Input Specifications."
12. Applies to Part Number MC8641xxx1000NX only. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V devices. Refer to Table 74 Part Numbering Nomenclature to determine if the device has been marked for V_{DD}_Core*n* = 0.95 V.
13. This voltage is the input to the filter discussed in Section 20.2, "Power Supply Design and Sequencing," and not necessarily the voltage at the AV_{DD}_Core*n* pin, which may be reduced from V_{DD}_Core*n* by the filter.

Figure 3 illustrates the Power Up sequence as described above.



Notes:

1. Dotted waveforms correspond to optional supply values for a specified power supply. See Table 2.
2. The recommended maximum ramp up time for power supplies is 20 milliseconds.
3. Refer to Section 5, "RESET Initialization" for additional information on PLL relock and reset signal assertion timing requirements.
4. Refer to Table 11 for additional information on reset configuration pin setup timing requirements. In addition see Figure 68 regarding HRESET and JTAG connection details including TRST.
5. e600 PLL relock time is 100 microseconds maximum plus 255 MPX_clk cycles.
6. Stable PLL configuration signals are required as stable SYSCLK is applied. All other POR configuration inputs are required 4 SYSCLK cycles before HRESET negation and are valid at least 2 SYSCLK cycles after HRESET has negated (hold requirement). See Section 5, "RESET Initialization" for more information on setup and hold time of reset configuration signals.
7. V$_{DD}$_PLAT, AV$_{DD}$_PLAT must strictly reach 90% of their recommended voltage before the rail for Dn_GV$_{DD}$, and Dn_MV$_{REF}$ reaches 10% of their recommended voltage.
8. SYSCLK must be driven only AFTER the power for the various power supplies is stable.
9. In device sleep mode, the reset configuration signals for DRAM types (TSEC2_TXD[4],TSEC2_TX_ER) must be valid BEFORE HRESET is asserted.

Figure 3. MPC8641 Power-Up and Reset Sequence

The maximum power dissipation for individual power supplies of the MPC8641D is shown in Table 5.

Table 5. MPC8641D Individual Supply Maximum Power Dissipation [1]

Component Description	Supply Voltage (Volts)	Power (Watts)	Notes
Per Core voltage Supply	V_{DD}_Core0/V_{DD}_Core1 = 1.1 V @ 1500 MHz	21.00	
Per Core PLL voltage supply	AV_{DD}_Core0/AV_{DD}_Core1 = 1.1 V @ 1500 MHz	0.0125	
Per Core voltage Supply	V_{DD}_Core0/V_{DD}_Core1 = 1.05 V @ 1333 MHz	17.00	
Per Core PLL voltage supply	AV_{DD}_Core0/AV_{DD}_Core1 = 1.05 V @ 1333 MHz	0.0125	
Per Core voltage Supply	V_{DD}_Core0/V_{DD}_Core1 = 0.95 V @ 1000 MHz	11.50	5
Per Core PLL voltage supply	AV_{DD}_Core0/AV_{DD}_Core1 = 0.95 V @ 1000 MHz	0.0125	5
DDR Controller I/O voltage supply	D*n*_GV_{DD} = 2.5 V @ 400 MHz	0.80	2
	D*n*_GV_{DD} = 1.8 V @ 533 MHz	0.68	2
	D*n*_GV_{DD} = 1.8 V @ 600 MHz	0.77	2
16-bit FIFO @ 200 MHz eTsec 1&2/3&4 Voltage Supply	L/TV_{DD} = 3.3 V	0.11	2, 3
non-FIFO eTsec*n* Voltage Supply	L/TV_{DD} = 3.3 V	0.08	2
x8 SerDes transceiver Supply	SV_{DD} = 1.1 V	0.70	2
x8 SerDes I/O Supply	XV_{DD}_SRDS*n* = 1.1 V	0.66	2
SerDes PLL voltage supply Port 1 or 2	AV_{DD}_SRDS1/AV_{DD}_SRDS2 = 1.1 V	0.10	
Platform I/O Supply	OV_{DD} = 3.3 V	0.45	4
Platform source Supply	V_{DD}_PLAT = 1.1 V @ 600 MHz	12.00	
Platform source Supply	V_{DD}_PLAT = 1.05 Vn @ 500 MHz	9.80	5
Platform source Supply	V_{DD}_PLAT = 1.05 Vn @ 400 MHz	7.70	
Platform, Local Bus PLL voltage Supply	AV_{DD}_PLAT, AV_{DD}_LB = 1.1 V	0.0125	

Notes:

1. This is a maximum power supply number which is provided for power supply and board design information. The numbers are based on 100% bus utilization for each component. The components listed are not expected to have 100% bus usage simultaneously for all components. Actual numbers may vary based on activity.
2. Number is based on a per port/interface value.
3. This is based on one eTSEC port used. Since 16-bit FIFO mode involves two ports, the number will need to be multiplied by two for the total. The other eTSEC protocols dissipate less than this number per port. Note that the power needs to be multiplied by the number of ports used for the protocol for the total eTSEC port power dissipation.
4. This includes Local Bus, DUART, I^2C, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, JTAG and Miscellaneous I/O voltage.
5. These power numbers are for Part Number MC8641xxx1000NX only. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V.

The power dissipation for the MPC8641 single core device is shown in Table 6.

Table 6. MPC8641 Power Dissipation (Single Core)

Power Mode	Core Frequency (MHz)	Platform Frequency (MHz)	V_{DD}_Coren, V_{DD}_PLAT (Volts)	Junction Temperature	Power (Watts)	Notes
Typical	1500 MHz	600 MHz	1.1 V	65 °C	20.3	1, 2
Thermal				105 °C	25.2	1, 3
Maxim					28.9	1, 4
Typical	1333 MHz	533 MHz	1.05 V	65 °C	16.3	1, 2
Thermal				105 °C	20.2	1, 3
Maximum					23.2	1, 4
Typical	1250 MHz	500 MHz	1.05 V	65 °C	16.3	1, 2
Thermal				105 °C	20.2	1, 3
Maximum					23.2	1, 4
Typical	1000 MHz	400 MHz	1.05 V	65 °C	16.3	1, 2
Thermal				105 °C	20.2	1, 3
Maximum					23.2	1, 4
Typical	1000 MHz	500 MHz	0.95 V, 1.05 V	65 °C	11.6	1, 2, 5
Thermal				105 °C	14.4	1, 3, 5
Maximum					16.5	1, 4, 5

Notes:

1. These values specify the power consumption at nominal voltage and apply to all valid processor bus frequencies and configurations. The values do not include power dissipation for I/O supplies.
2. Typical power is an average value measured at the nominal recommended core voltage (V_{DD}_Core*n*) and 65°C junction temperature (see Table 2)while running the Dhrystone 2.1 benchmark and achieving 2.3 Dhrystone MIPs/MHz.
3. Thermal power is the average power measured at nominal core voltage (V_{DD}_Core*n*) and maximum operating junction temperature (see Table 2) while running the Dhrystone 2.1 benchmark and achieving 2.3 Dhrystone MIPs/MHz and a typical workload on platform interfaces.
4. Maximum power is the maximum power measured at nominal core voltage (V_{DD}_Core*n*) and maximum operating junction temperature (see Table 2) while running a test which includes an entirely L1-cache-resident, contrived sequence of instructions which keep all the execution units maximally busy.
5. These power numbers are for Part Number MC8641xx1000NX only. V_{DD}_Core*n* = 0.95 V and V_{DD}_PLAT = 1.05 V.

4 Input Clocks

Table 7 provides the system clock (SYSCLK) DC specifications for the MPC8641.

Table 7. SYSCLK DC Electrical Characteristics (OVDD = 3.3 V ± 165 mV)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

4.1 System Clock Timing

Table 8 provides the system clock (SYSCLK) AC timing specifications for the MPC8641.

Table 8. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV_{DD} = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	66	—	166.66	MHz	1
SYSCLK cycle time	t_{SYSCLK}	6	—	—	ns	—
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	150	ps	4, 5

Notes:
1. **Caution:** The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 18.2, “MPX to SYSCLK PLL Ratio,” and Section 18.3, “e600 to MPX clock PLL Ratio,” for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.4 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the short term jitter only and is guaranteed by design.
5. The SYSCLK driver’s closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter. Note that the frequency modulation for SYSCLK reduces significantly for the spread spectrum source case. This is to guarantee what is supported based on design.

4.1.1 SYSCLK and Spread Spectrum Sources

Spread spectrum clock sources are an increasingly popular way to control electromagnetic interference emissions (EMI) by spreading the emitted noise to a wider spectrum and reducing the peak noise magnitude in order to meet industry and government requirements. These clock sources intentionally add long-term jitter in order to diffuse the EMI spectral content. The jitter specification given in Table 8 considers short-term (cycle-to-cycle) jitter only and the clock generator’s cycle-to-cycle output jitter

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 18 provides the input AC timing specifications for the DDR2 SDRAM when D*n*_GV_{DD}(typ)=1.8 V.

Table 18. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage 400, 533 MHz 600 MHz	V_{IL}	—	 D*n*_MV_{REF} – 0.25 D*n*_MV_{REF} – 0.20	V	—
AC input high voltage 400, 533 MHz 600 MHz	V_{IH}	 D*n*_MV_{REF} + 0.25 D*n*_MV_{REF} + 0.20	—	V	—

Table 19 provides the input AC timing specifications for the DDR SDRAM when D*n*_GV_{DD}(typ)=2.5 V.

Table 19. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	D*n*_MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	D*n*_MV_{REF} + 0.31	—	V	—

Table 20 provides the input AC timing specifications for the DDR SDRAM interface.

Table 20. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC	t_{CISKEW}	—		ps	1, 2
600 MHz	—	–240	240	—	3
533 MHz	—	–300	300	—	3
400 MHz	—	–365	365	—	—

Note:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}.This can be determined by the following equation: t_{DISKEW} =+/–(T/4 – abs(t_{CISKEW})) where T is the clock period and abs(t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. Maximum DDR1 frequency is 400 MHz.

Table 28. GMII Transmit AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
GTX_CLK data clock fall time (80%-20%)	t_{GTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 10 shows the GMII transmit AC timing diagram.

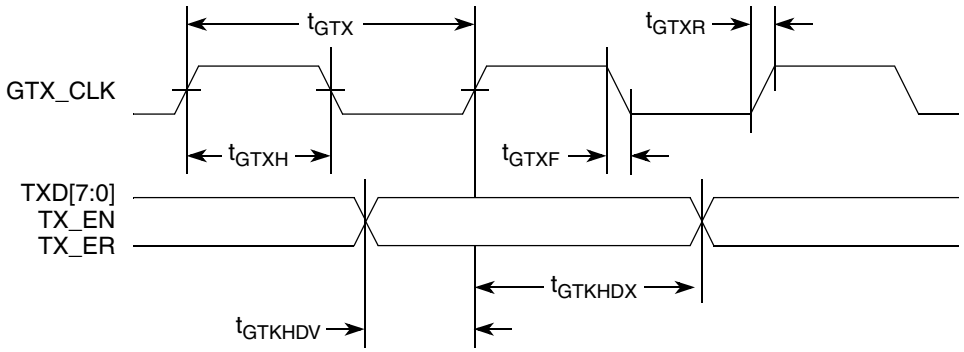


Figure 10. GMII Transmit AC Timing Diagram

8.2.2.2 GMII Receive AC Timing Specifications

Table 29 provides the GMII receive AC timing specifications.

Table 29. GMII Receive AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}[3]	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	ns
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise time (20%-80%)	t_{GRXR}[2]	—	—	1.0	ns

8.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.7.1 RMII Transmit AC Timing Specifications

The RMII transmit AC timing specifications are in Table 36.

Table 36. RMII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
REF_CLK clock period	t_{RMT}	—	20.0	—	ns
REF_CLK duty cycle	t_{RMTH}/t_{RMT}	35	50	65	%
REF_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time REF_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time REF_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns
REF_CLK to RMII data TXD[1:0], TX_EN delay	t_{RMTDX}	1.0	—	10.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 20 shows the RMII transmit AC timing diagram.

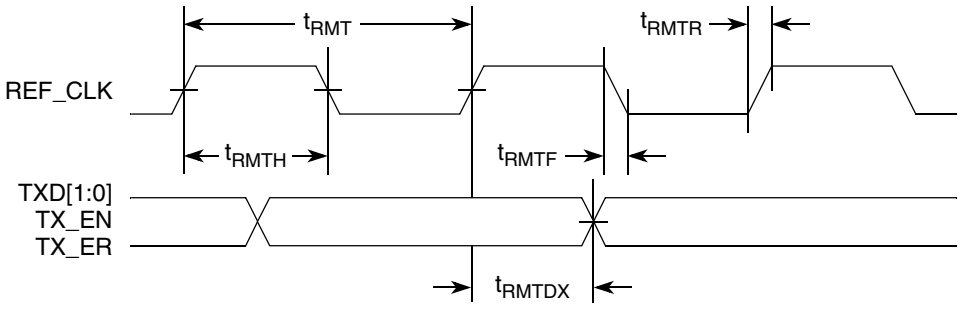


Figure 20. RMII Transmit AC Timing Diagram

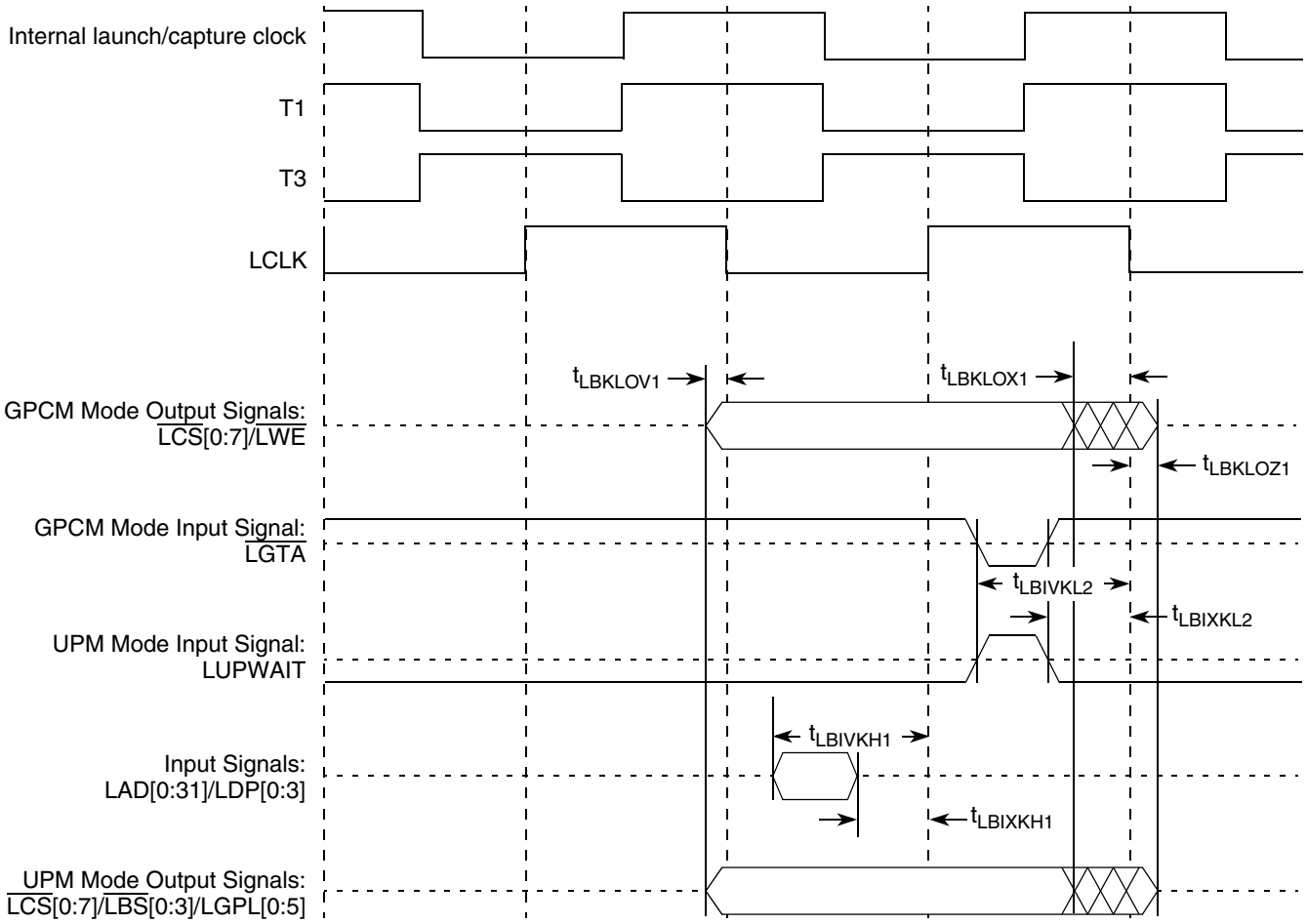


Figure 29. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (clock ratio of 4) (PLL Bypass Mode)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the MPC8641/D.

11.1 JTAG DC Electrical Characteristics

Table 43 provides the DC electrical characteristics for the JTAG interface.

Table 43. JTAG DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	– 0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –100 μA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 100 μA)	V_{OL}	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

11.2 JTAG AC Electrical Specifications

Table 44 provides the JTAG AC timing specifications as defined in Figure 33 through Figure 35.

Table 44. JTAG AC Timing Specifications (Independent of SYSCLK) [1]

At recommended operating conditions (see Table 3).

Parameter	Symbol [2]	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f_{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t_{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t_{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t_{JTGR} & t_{JTGF}	0	2	ns	6
$\overline{TRST}$ assert time	t_{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	 t_{JTDVKH} t_{JTIVKH}	 4 0	 — —	ns	4
Input hold times: Boundary-scan data TMS, TDI	 t_{JTDXKH} t_{JTIXKH}	 20 25	 — —	ns	4
Valid times: Boundary-scan data TDO	 t_{JTKLDV} t_{JTKLOV}	 4 4	 20 25	ns	5

To illustrate these definitions using real values, consider the case of a CML (Current Mode Logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{\text{TD}}$, has a swing that goes between 2.5 V and 2.0 V. Using these values, the peak-to-peak voltage swing of each signal (TD or $\overline{\text{TD}}$) is 500 mV p-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 mV and –500 mV, in other words, V_{OD} is 500 mV in one phase and –500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage ($V_{DIFFp-p}$) is 1000 mV p-p.

13.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks inputs are SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ for PCI Express and Serial RapidIO.

The following sections describe the SerDes reference clock requirements and some application information.

13.2.1 SerDes Reference Clock Receiver Characteristics

Figure 39 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XV_{DD}_SRDS*n* are specified in Table 1 and Table 2.
- SerDes Reference Clock Receiver Reference Circuit Structure
  - The SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 39. Each differential clock input (SD*n*_REF_CLK or $\overline{\text{SD}n\text{\_REF\_CLK}}$) has a 50-Ω termination to SGND followed by on-chip AC-coupling.
  - The external reference clock driver must be able to drive this termination.
  - The SerDes reference clock input can be either differential or single-ended. Refer to the Differential Mode and Single-ended Mode description below for further detailed requirements.
- The maximum average current requirement that also determines the common mode voltage range
  - When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (refer to the following bullet for more detail), since the input is AC-coupled on-chip.
  - This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND. For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 mA to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
  - If the device driving the SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ inputs cannot drive 50 Ω to SGND DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.

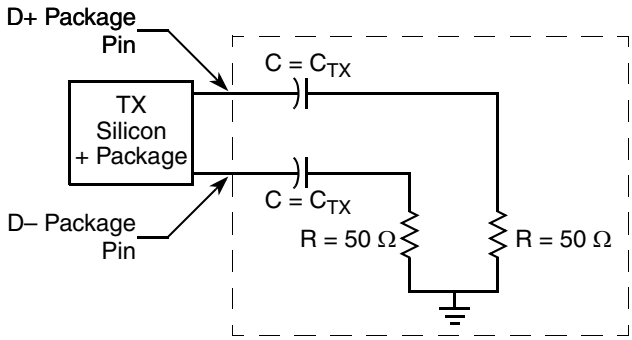


Figure 52. Compliance Test/Measurement Load

15 Serial RapidIO

This section describes the DC and AC electrical specifications for the RapidIO interface of the MPC8641, for the LP-Serial physical layer. The electrical specifications cover both single and multiple-lane links. Two transmitter types (short run and long run) on a single receiver are specified for each of three baud rates, 1.25, 2.50, and 3.125 GBaud.

Two transmitter specifications allow for solutions ranging from simple board-to-board interconnect to driving two connectors across a backplane. A single receiver specification is given that will accept signals from both the short run and long run transmitter specifications.

The short run transmitter specifications should be used mainly for chip-to-chip connections on either the same printed circuit board or across a single connector. This covers the case where connections are made to a mezzanine (daughter) card. The minimum swings of the short run specification reduce the overall power used by the transceivers.

The long run transmitter specifications use larger voltage swings that are capable of driving signals across backplanes. This allows a user to drive signals across two connectors and a backplane. The specifications allow a distance of at least 50 cm at all baud rates.

All unit intervals are specified with a tolerance of +/– 100 ppm. The worst case frequency difference between any transmit and receive clock will be 200 ppm.

To ensure interoperability between drivers and receivers of different vendors and technologies, AC coupling at the receiver input must be used.

15.1 DC Requirements for Serial RapidIO SD*n*_REF_CLK and SD*n*_REF_CLK

For more information, see Section 13.2, “SerDes Reference Clocks.”

15.2 AC Requirements for Serial RapidIO SD*n*_REF_CLK and SD*n*_REF_CLK

Table 51 lists AC requirements.

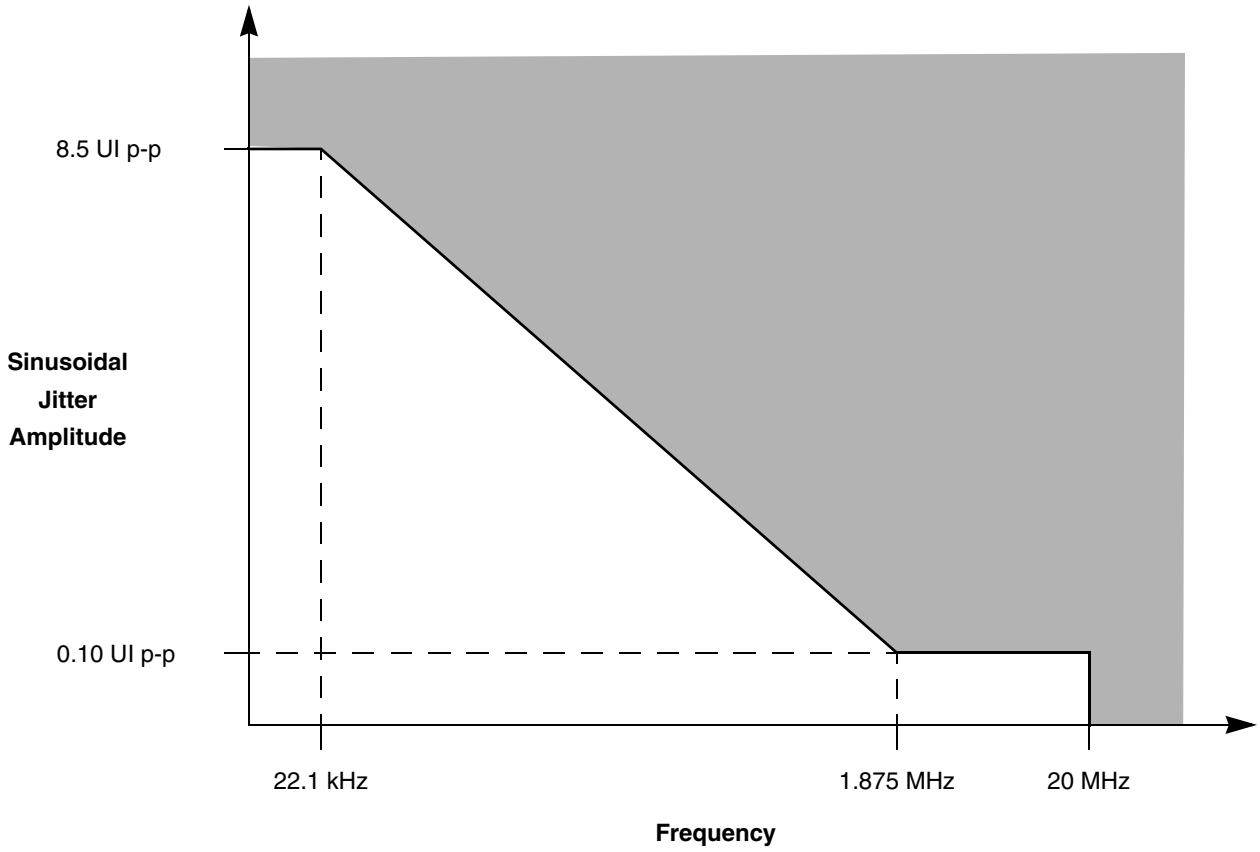


Figure 55. Single Frequency Sinusoidal Jitter Limits

15.8 Receiver Eye Diagrams

For each baud rate at which an LP-Serial receiver is specified to operate, the receiver shall meet the corresponding Bit Error Rate specification (Table 59, Table 60, Table 61) when the eye pattern of the receiver test signal (exclusive of sinusoidal jitter) falls entirely within the unshaded portion of the Receiver Input Compliance Mask shown in Figure 56 with the parameters specified in Table . The eye pattern of the receiver test signal is measured at the input pins of the receiving device with the device replaced with a 100 Ω +/– 5% differential resistive load.

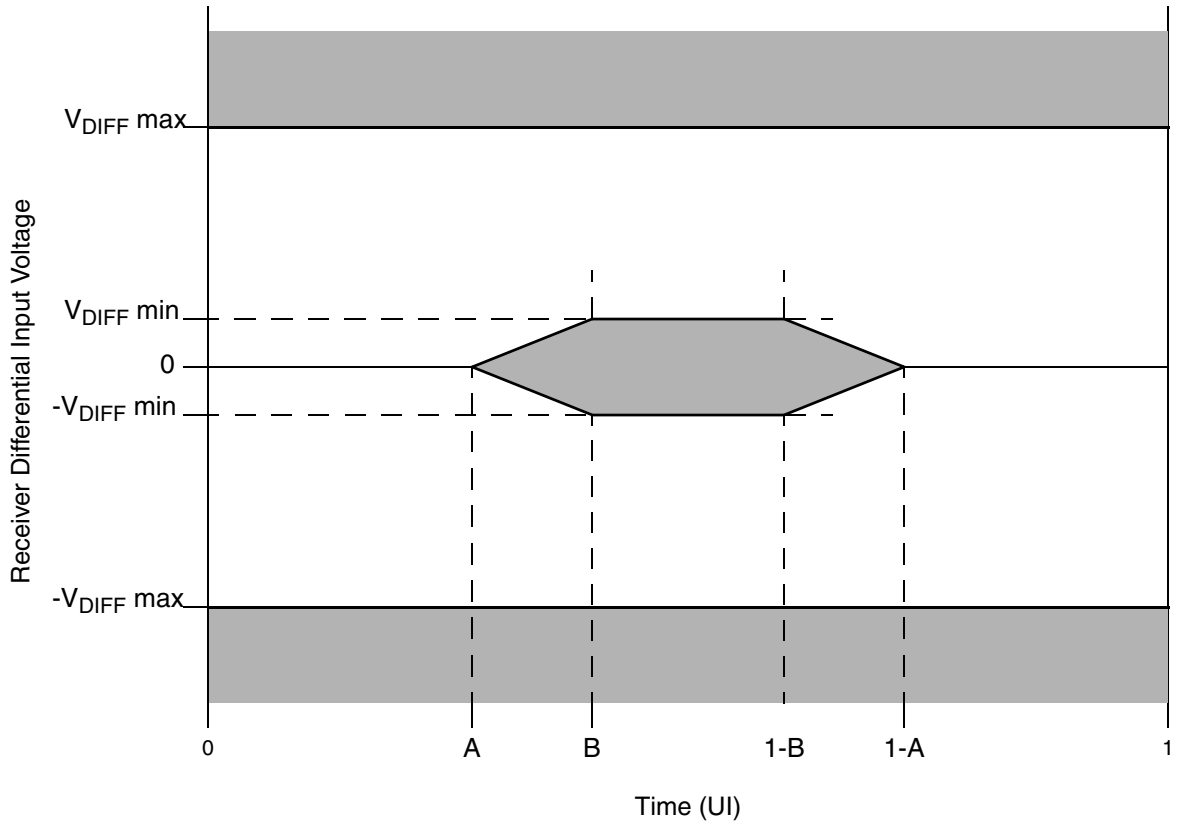


Figure 56. Receiver Input Compliance Mask

Table 62. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

Receiver Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

15.9 Measurement and Test Requirements

Since the LP-Serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. In addition, the CJPAT test pattern defined in Annex 48A of IEEE 802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

15.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for template measurements is the

17 Signal Listings

Table 63 provides the pin assignments for the signals. Notes for the signal changes on the single core device (MPC8641) are italicized and prefixed by *"S"*.

Table 63. MPC8641 Signal Reference by Functional Block

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
DDR Memory Interface 1 Signals[2,3]				
D1_MDQ[0:63]	D15, A14, B12, D12, A15, B15, B13, C13, C11, D11, D9, A8, A12, A11, A9, B9, F11, G12, K11, K12, E10, E9, J11, J10, G8, H10, L9, L7, F10, G9, K9, K8, AC6, AC7, AG8, AH9, AB6, AB8, AE9, AF9, AL8, AM8, AM10, AK11, AH8, AK8, AJ10, AK10, AL12, AJ12, AL14, AM14, AL11, AM11, AM13, AK14, AM15, AJ16, AK18, AL18, AJ15, AL15, AL17, AM17	I/O	$D1\_GV_{DD}$	—
D1_MECC[0:7]	M8, M7, R8, T10, L11, L10, P9, R10	I/O	$D1\_GV_{DD}$	—
D1_MDM[0:8]	C14, A10, G11, H9, AD7, AJ9, AM12, AK16, N10	O	$D1\_GV_{DD}$	—
D1_MDQS[0:8]	A13, C10, H12, J7, AE8, AM9, AK13, AK17, N9	I/O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MDQS}}$[0:8]	D14, B10, H13, J8, AD8, AL9, AJ13, AM16, P10	I/O	$D1\_GV_{DD}$	—
D1_MBA[0:2]	AA8, AA10, T9	O	$D1\_GV_{DD}$	—
D1_MA[0:15]	Y10, W8, W9, V7, V8, U6, V10, U9, U7, U10, Y9, T6, T8, AE12, R7, P6	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MWE}}$	AB11	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MRAS}}$	AB12	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCAS}}$	AC10	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCS}}$[0:3]	AB9, AD10, AC12, AD11	O	$D1\_GV_{DD}$	—
D1_MCKE[0:3]	P7, M10, N8, M11	O	$D1\_GV_{DD}$	23
D1_MCK[0:5]	W6, E13, AH11, Y7, F14, AG10	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCK}}$[0:5]	Y6, E12, AH12, AA7, F13, AG11	O	$D1\_GV_{DD}$	—
D1_MODT[0:3]	AC9, AF12, AE11, AF10	O	$D1\_GV_{DD}$	—
D1_MDIC[0:1]	E15, G14	IO	$D1\_GV_{DD}$	27
$D1\_MV_{REF}$	AM18	DDR Port 1 reference voltage	$D1\_GV_{DD}$ /2	3
DDR Memory Interface 2 Signals[2,3]				

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
$SENSEV_{SS}$_Core0	P14	Core0 GND sensing pin	—	31
$SENSEV_{SS}$_Core1	V20	Core1 GND sensing pin	—	12, 31, *S3*
$SENSEV_{DD}$_PLAT	N18	V_{DD}_PLAT sensing pin	—	28
$SENSEV_{SS}$_PLAT	P18	Platform GND sensing pin	—	29
$D1\_GV_{DD}$	B11, B14, D10, D13, F9, F12, H8, H11, H14, K10, K13, L8, P8, R6, U8, V6, W10, Y8, AA6, AB10, AC8, AD12, AE10, AF8, AG12, AH10, AJ8, AJ14, AK12, AL10, AL16	SDRAM 1 I/O supply	$D1\_GV_{DD}$ 2.5 - DDR 1.8 DDR2	—
$D2\_GV_{DD}$	B2, B5, B8, D4, D7, E2, F6, G4, H2, J6, K4, L2, M6, N4, P2, T4, U2, W4, Y2, AB4, AC2, AD6, AE4, AF2, AG6, AH4, AJ2, AK6, AL4, AM2	SDRAM 2 I/O supply	$D2\_GV_{DD}$ 2.5 V - DDR 1.8 V - DDR2	—
OV_{DD}	B22, B25, B28, D17, D24, D27, F19, F22, F26, F29, G17, H21, H24, K19, K23, M21, AM30	DUART, Local Bus, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, JTAG, Power management, I^2C, JTAG and Miscellaneous I/O voltage	OV_{DD} 3.3 V	—
LV_{DD}	AC20, AD23, AH22	TSEC1 and TSEC2 I/O voltage	LV_{DD} 2.5/3.3 V	—
TV_{DD}	AC17, AG18, AK20	TSEC3 and TSEC4 I/O voltage	TV_{DD} 2.5/3.3 V	—
SV_{DD}	H31, J29, K28, K32, L30, M28, M31, N29, R30, T31, U29, V32, W30, Y31, AA29, AB32, AC30, AD31, AE29, AG30, AH31, AJ29, AK32, AL30, AM31	Transceiver Power Supply SerDes	SV_{DD} 1.05/1.1 V	—
XV_{DD}_SRDS1	K26, L24, M27, N25, P26, R24, R28, T27, U25, V26	Serial I/O Power Supply for SerDes Port 1	XV_{DD}_SRDS1 1.05/1.1 V	—

example, assuming a T_i of 30°C, a T_r of 5°C, a package $R_{\theta JC}$ = 0.1, and a typical power consumption (P_d) of 43.4 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 0.2°C/W + \theta_{sa}) \times 43.4\ W$

For this example, a $R_{\theta sa}$ value of 1.32 °C/W or less is required to maintain the die junction temperature below the maximum value of Table 2.

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, and so on.

Due to the complexity and variety of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board as well as system-level designs.

For system thermal modeling, the MPC8641 thermal model is shown in Figure 62. Four cuboids are used to represent this device. The die is modeled as 12.4x15.3 mm at a thickness of 0.86 mm. See Section 3, "Power Characteristics" for power dissipation details. The substrate is modeled as a single block 33x33x1.2 mm with orthotropic conductivity: 13.5 W/(m • K) in the xy-plane and 5.3 W/(m • K) in the z-direction. The die is centered on the substrate. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate with a conductivity of 5.3 W/(m • K) in the thickness dimension of 0.07 mm. Because the bump/underfill is modeled with zero physical dimension (collapsed height), the die thickness was slightly enlarged to provide the correct height. The C5 solder layer is modeled as a cuboid with dimensions 33x33x0.4 mm and orthotropic thermal conductivity of 0.034 W/(m • K) in the xy-plane and 9.6 W/(m • K) in the z-direction. An LGA solder layer would be modeled as a collapsed thermal resistance with thermal conductivity of 9.6W/(m • K) and an effective height of 0.1 mm. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.

designer place at least one decoupling capacitor at each OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT pin of the device. These decoupling capacitors should receive their power from separate OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT and GND power planes in the PCB, utilizing short traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT planes, to enable quick recharging of the smaller chip capacitors. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON).

20.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}_SRDS*n*) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

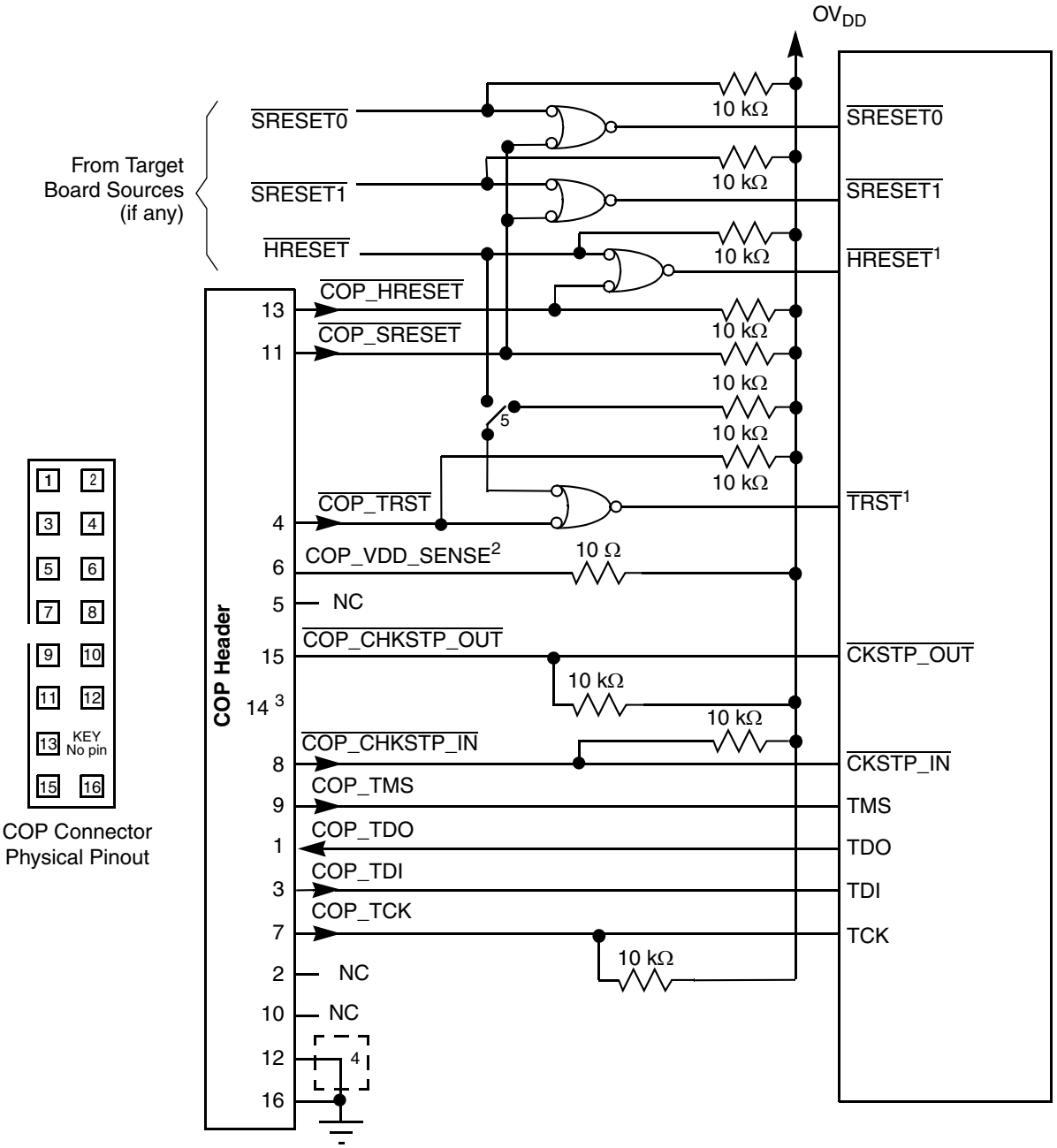
- First, the board should have at least 10 x 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

20.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. In general all unused active low inputs should be tied to OV_{DD}, D*n*_GV_{DD}, LV_{DD}, TV_{DD}, V_{DD}_Core*n*, and V_{DD}_PLAT, XV_{DD}_SRDS*n*, and SV_{DD} as required and unused active high inputs should be connected to GND. All NC (no-connect) signals must remain unconnected.

Special cases:

DDR - If one of the DDR ports is not being used the power supply pins for that port can be connected to ground so that there is no need to connect the individual unused inputs of that port to ground. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port. Power supplies for other functional buses should remain powered.



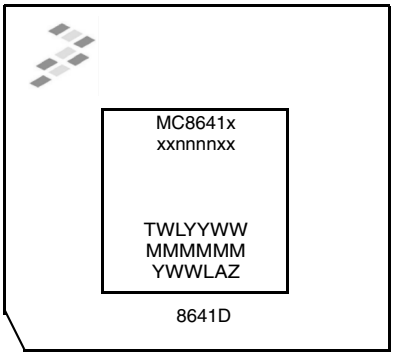
Notes:

1. The COP port and target board should be able to independently assert $\overline{\text{HRESET}}$ and $\overline{\text{TRST}}$ to the processor in order to fully control the processor as shown here.
2. Populate this with a 10 Ω resistor for short-circuit/current-limiting protection.
3. The KEY location (pin 14) is not physically present on the COP header.
4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
5. This switch is included as a precaution for BSDL testing. The switch should be open during BSDL testing to avoid accidentally asserting the $\overline{\text{TRST}}$ line. If BSDL testing is not being performed, this switch should be closed or removed.

Figure 68. JTAG/COP Interface Connection for one MPC8641 device

21.2 Part Marking

Parts are marked as the example shown in Figure 70.



NOTE:
TWLYYWW is the test code
MMMMMM is the M00 (mask) number.
YWWLAZ is the assembly traceability code.

Figure 70. Part Marking for FC-CBGA Device

22 Document Revision History

Table 76 provides a revision history for the MPC8641D hardware specification.

Table 76. Document Revision History

Revision	Date	Substantive Change(s)
3	05/2014	• Updated the Serial RapidIO equation in Section 4.4, “Platform Frequency Requirements for PCI-Express and Serial RapidIO” • Updated Section 19.2.4, “Temperature Diode,” by removing the ideality factor value. • Added VJ package type designator and footnotes to Table 74, “Part Numbering Nomenclature” and Section 16.1, “Package Parameters for the MPC8641.”
2	07/2009	• Added note 8 to Table 49, “Differential Transmitter (TX) Output Specifications.” • Added Revision E to Table 74, “Part Numbering Nomenclature.”
1	11/2008	• Added Section 4.4, “Platform Frequency Requirements for PCI-Express and Serial RapidIO.” • Removed the statement “Note that core processor speed of 1500 MHz is only available for the MPC8641D (dual core)” from Note 2 in Table 74 because a 1500 MHz core is offered for both MPC8641D (dual core) and MPC8641 (single core). • Added Note 8 to Figure 57 and Figure 58.
0	07/2008	• Initial Release